

SCHOTTKY DIE SPECIFICATION

General Description: 100 V 1 A (Low Ir)

TYPE: MBR1100S

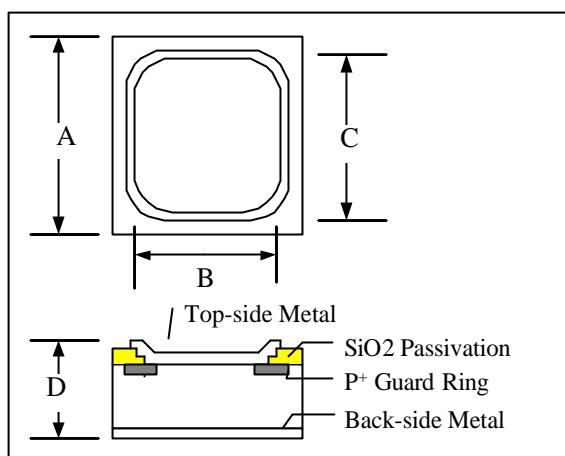
Single Anode

ELECTRICAL CHARACTERISTICS		SYM	Spec. Limit	Die Sort	UNIT
DC Blocking Voltage:	Ir=1mA(for wafer form)	VRRM	100	105	Volt
	Ir=0.5mA (for dice form)				
Average Rectified Forward Current		IFAV	1		Amp
Maximum Instantaneous Forward Voltage @ 1 Amperes, Ta=25°C		VF MAX	0.85	0.84	Volt
Maximum Instantaneous Reverse Voltage VR= 100 Volt, Ta=25°C		IR MAX	0.05	0.045	mA
Maximum Junction Capacitance @ 0V, 1MHZ		Cj MAX			pF
MAXIMUM RATINGS					
Nonrepetitive Peak Surge Current		IFSM	25		Amp
Operating Junction Temperature		Tj	-65 to +125		°C
Storage Temperatures		TSTG	-65 to +125		°C

Specification apply to die only. Actual performance may degrade when assembled.

MEMT does not guarantee device performance after assembly.

Data sheet information is subjected to change without notice.

DICE OUTLINE DRAWING


DIM	ITEM	um²	Mil²
A	Die Size	914	35.98
B	Top Metal Pad Size	814	32.0
C	Passivation Seal	834	32.8
D	Thickness (Min)	254	10
	Thickness (Max)	305	12

PS:

- (1)Cutting street width is around 80um(3.14mil).
(2)Both of top-side and back-side metals are Ti/Ni/Ag.